

HSM124S

Silicon Epitaxial Planar Diode for Switching

HITACHI

Rev. 4
Aug. 1995

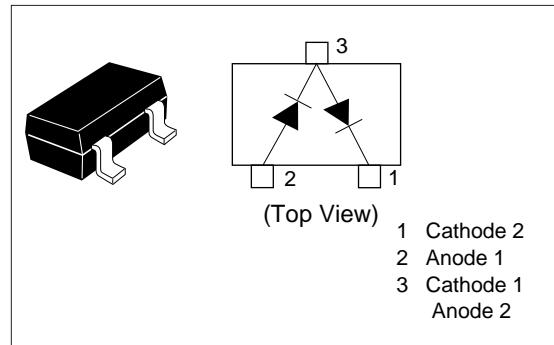
Features

- Low reverse current.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM124S	A 1	MPAK

Pin Arrangement



Absolute Maximum Ratings ** (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V _R	80	V
Peak reverse voltage	V _{RM}	85	V
Peak forward current	I _{FM}	300	mA
Non-Repetitive peak forward surge current	I _{FSM} *	4	A
Average forward current	I _o	100	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

* Within 1μs forward surge current.

** Per one device

Electrical Characteristics *(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V _{F1}	—	—	1.0		I _F = 10 mA
	V _{F2}	—	—	1.0	V	I _F = 50 mA
	V _{F3}	—	—	1.2		I _F = 100 mA
Reverse current	I _R	—	—	0.01	μA	V _R = 80 V
Capacitance	C	—	—	4.0	pF	V _R = 0 V, f = 1 MHz
Reverse recovery time	trr	—	—	100	ns	I _F = 10mA, V _R = 6V, R _L = 50Ω

* Per one device

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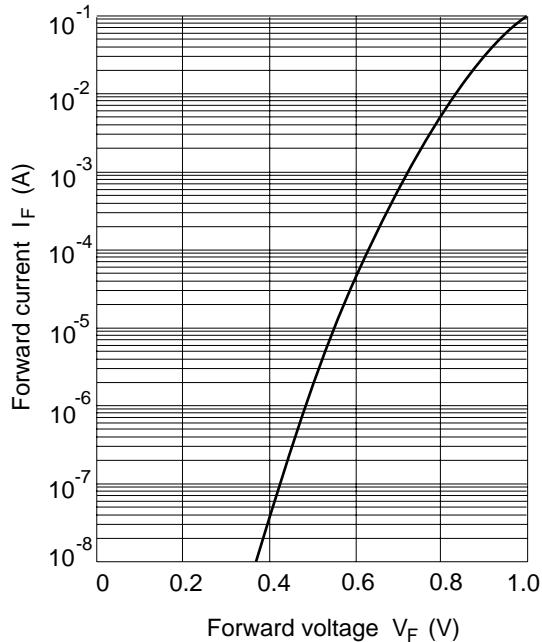


Fig.1 Forward current Vs.
Forward voltage

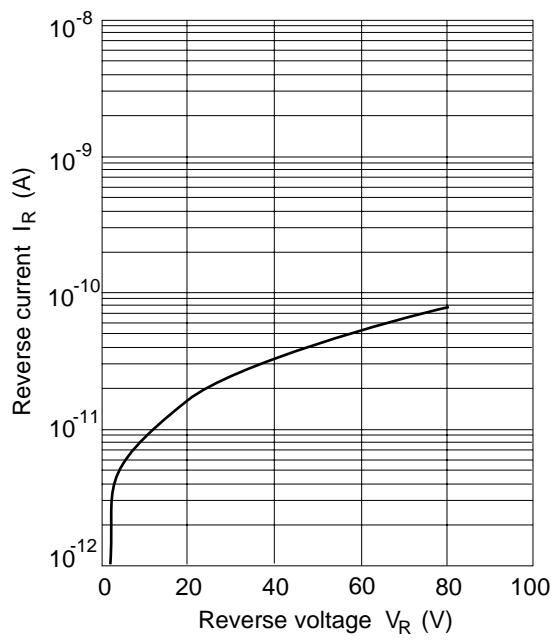


Fig.2 Reverse current Vs.
Reverse voltage

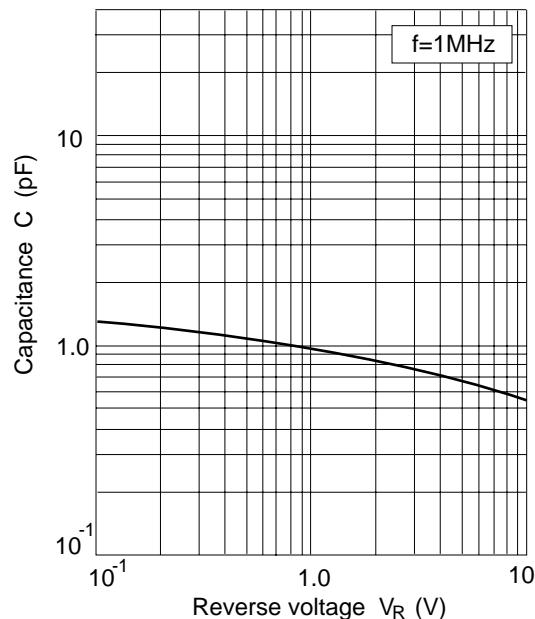


Fig.3 Capacitance Vs.
Reverse voltage

Package Dimensions

Unit: mm

